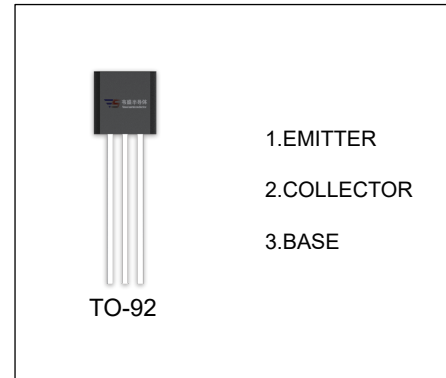


MPSA14 TRANSISTOR (NPN)

FEATURES

- Darlington Transistor



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
MPSA14	TO-92	Bulk	1000pcs/Bag
MPSA14-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	30	V
V _{CE0}	Collector-Emitter Voltage	30	V
V _{EB0}	Emitter-Base Voltage	10	V
I _C	Collector Current -Continuous	0.5	A
P _D	Collector Power Dissipation	625	mW
R _{θ JA}	Thermal Resistance from Junction to Ambient	200	°C /W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

$T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1\text{mA}, I_E=0$	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1\text{mA}, I_C=0$	10			V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=10\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=5\text{V}, I_C=10\text{mA}$	10000			
	$h_{FE(2)}^*$	$V_{CE}=5\text{V}, I_C=100\text{mA}$	20000			
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C=100\text{mA}, I_B=0.1\text{mA}$			1.5	V
Base-emitter voltage	V_{BE}^*	$V_{CE}=5\text{V}, I_C=100\text{mA}$			2.0	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	125			MHz

*Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2.0\%$.

